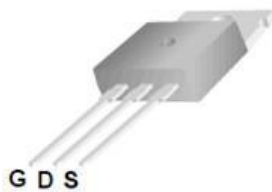


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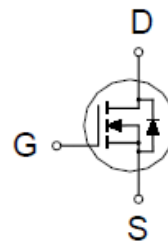
N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
100V	$18m\Omega @ V_{GS} = 10V$	63A



TO-220



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ²	$T_C = 25\text{ }^\circ\text{C}$	I_D	63	A
	$T_C = 100\text{ }^\circ\text{C}$		40	
Pulsed Drain Current ¹		I_{DM}	180	
Avalanche Current		I_{AS}	87	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	380	mJ
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	166	W
	$T_C = 100\text{ }^\circ\text{C}$		66	
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		0.75	$^\circ\text{C} / \text{W}$
Junction-to-Ambient	$R_{\theta JA}$		62.5	

¹Pulse width limited by maximum junction temperature.

²Limited by package.

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100V, V _{GS} = 0V			1	μA
		V _{DS} = 80V, V _{GS} = 0V, T _J = 125 °C			25	
On-State Drain Current ¹	I _{D(ON)}	V _{DS} = 10V, V _{GS} = 10V	180			A
Drain-Source On-State	R _{DS(ON)}	V _{GS} = 10V, I _D = 32A		16	18	mΩ
Forward Transconductance ¹	g _{fs}	V _{DS} = 50V, I _D = 32A		85		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz		4060		nF
Output Capacitance	C _{oss}			617		
Reverse Transfer Capacitance	C _{riss}			74		
Total Gate Charge ²	Q _g	V _{DS} = 50V, V _{GS} = 10V, I _D = 32A		93		nC
Gate-Source Charge ²	Q _{gs}			18		
Gate-Drain Charge ²	Q _{gd}			34		
Turn-On Delay Time ²	t _{d(on)}	V _{DD} = 15V, I _D ≅ 32A, V _{GS} = 10V, R _{GEN} = 6Ω		10		nS
Rise Time ²	t _r			250		
Turn-Off Delay Time ²	t _{d(off)}			210		
Fall Time ²	t _f			250		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current ³	I _S				63	A
Forward Voltage ¹	V _{SD}	I _F = 32A, V _{GS} = 0V			1.2	V
Reverse Recovery Time	t _{rr}	V _{GS} = 0V, I _F = 32A, di _F /dt = 100A / μS		158		nS
Reverse Recovery Charge	Q _{rr}				0.6	

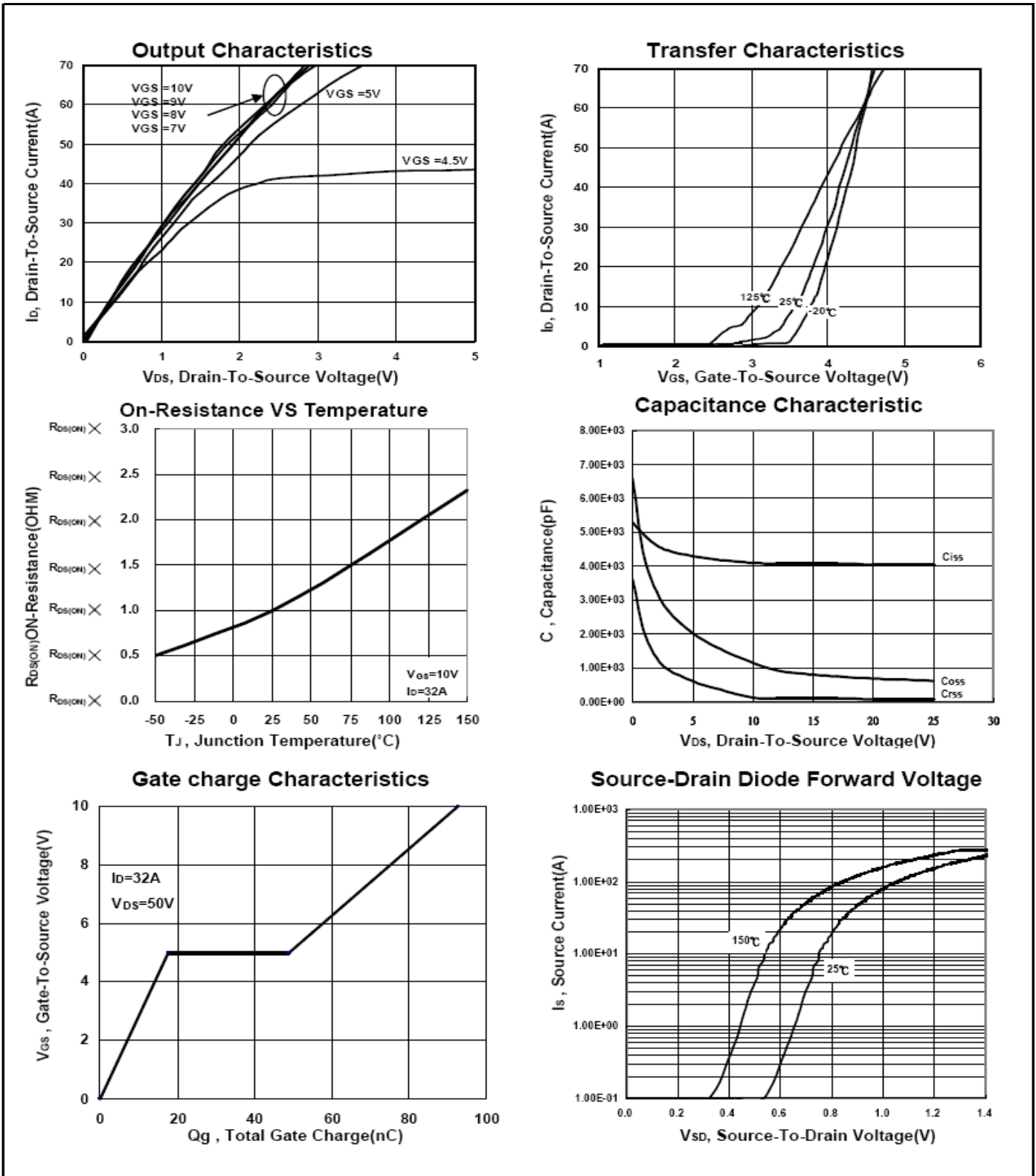
¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

³Limited by maximum junction temperature.

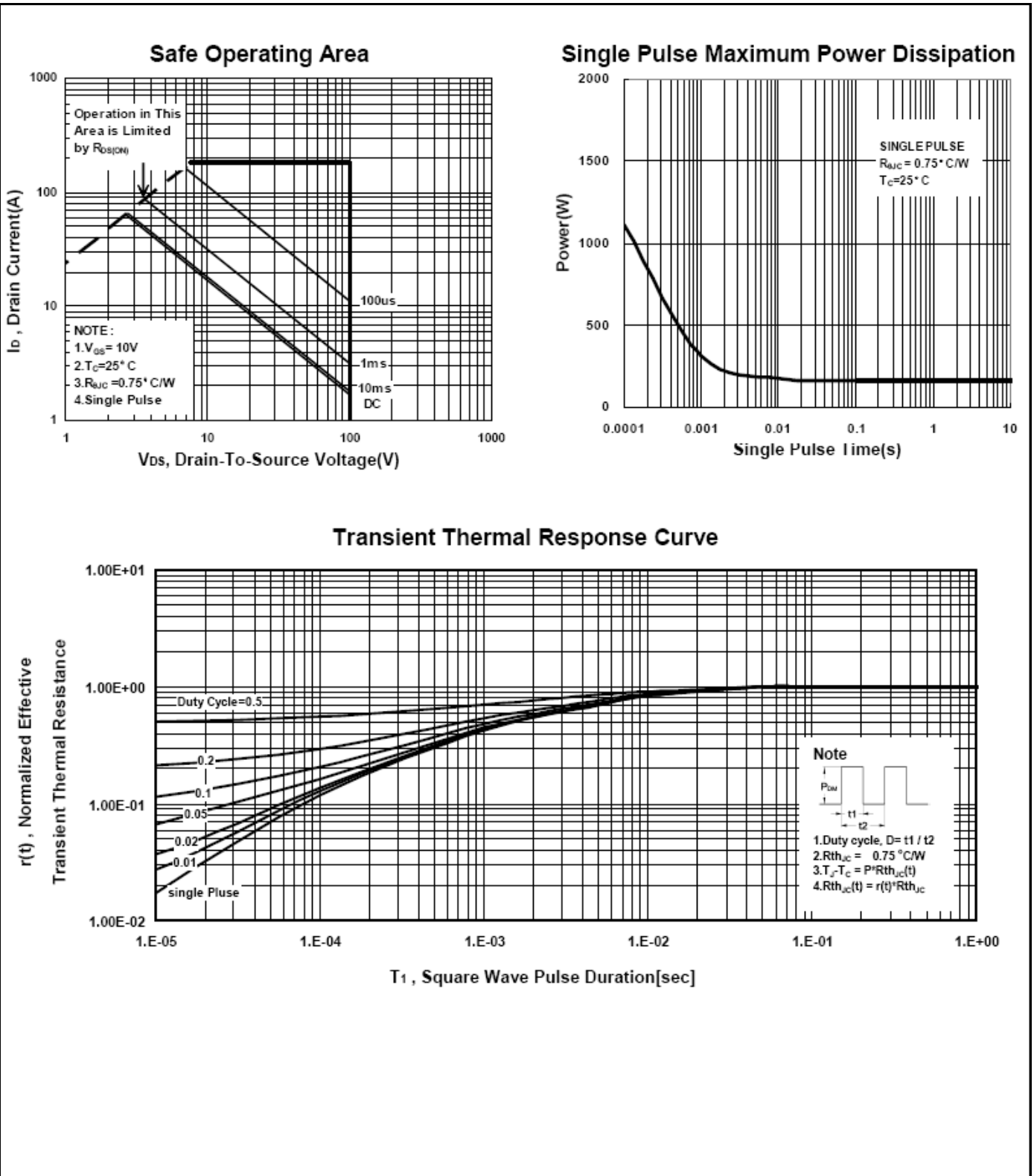
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Package Dimension

TO-220 (3-Lead) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	9.652	10.16	11.5	H	2.04	2.54	3.04
B	2.54	2.79	3.048	I	1.15	1.52	1.778
C	17.3		22.86	J	3.556	4.57	4.826
D	26.924	29.03	31.242	K	0.508	1.3	1.45
E	14.224	15.45	16.510	L	1.89	2.69	3.09
F	8.382	9.20	9.40	M	0.34	0.5	0.6
G	0.381	0.81	1.016	N			

